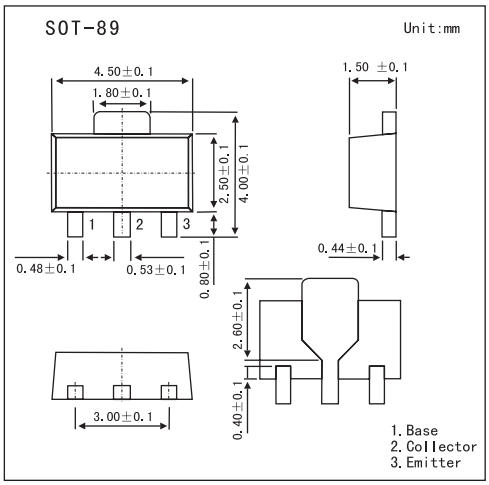
Surface Mount PNP Switching Transistor
CXT2907A



■ Features

- High current (max.600mA)
- Low voltage (max.60V)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current (DC)	I_C	-600	mA
Power dissipation	P_D	1.2	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-65 to +150	℃
Thermal Resistance	θ_{JA}	104	℃/W

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cut-off current	I_{CBO}	I_E = 0; V_{CB} = -50 V			-10	nA
		I_E = 0; V_{CB} = -50 V; T_j = 125 ℃			-10	μA
Emitter-base cut-off current	I_{EBO}	I_C = 0; V_{EB} = -5 V			-50	nA
DC current gain	h_{FE}	I_C = -0.1 mA; V_{CE} = -10 V	75			
		I_C = -1 mA; V_{CE} = -10 V	100			
		I_C = -10 mA; V_{CE} = -10 V	100			
		I_C = -150 mA; V_{CE} = -10 V	100		300	
		I_C = -500 mA; V_{CE} = -10 V	50			
Collector-emitter saturation voltage	V_{CEsat}	I_C = -150 mA; I_B =-15mA			-0.4	V
		I_C = -500 mA; I_B = -50 mA			-1.6	V
Base-emitter saturation voltage	V_{BEsat}	I_C = -150 mA; I_B = -15 mA			-1.3	V
		I_C = -500 mA; I_B = -50 mA			-2.6	V
Turn-on time	t_{on}	V_{CC}=30V, V_{BE}=-0.5V,I_C=-150mA, I_{B1}=-15mA			45	ns
Delay time	t_d				10	ns
Rise time	t_r				40	ns
Turn-off time	t_{off}	V_{CC}=-6.0V,I_C=-150mA, I_{B1}=I_{B2}=-15mA			100	ns
Storage time	t_s				80	ns
Fall time	t_f				30	ns
Transition frequency	f_T	I_C = -50 mA; V_{CE} = -20 V; f = 100 MHz	200			MHz

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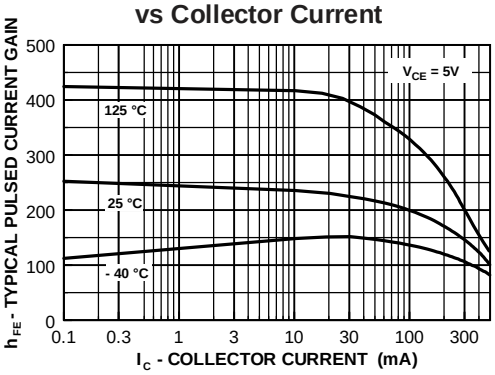
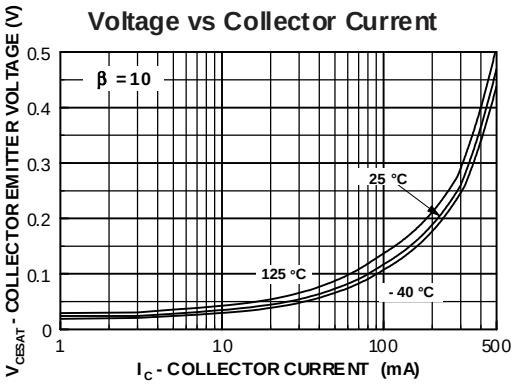
Typical Characteristics

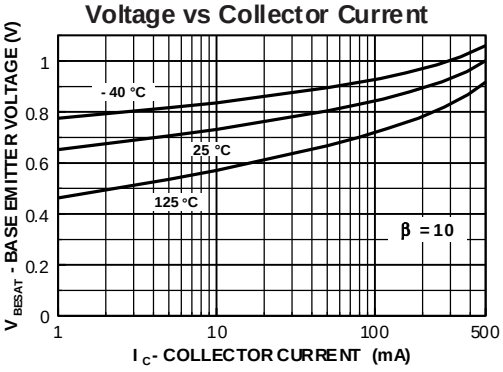
Typical Pulsed Current Gain vs Collector Current



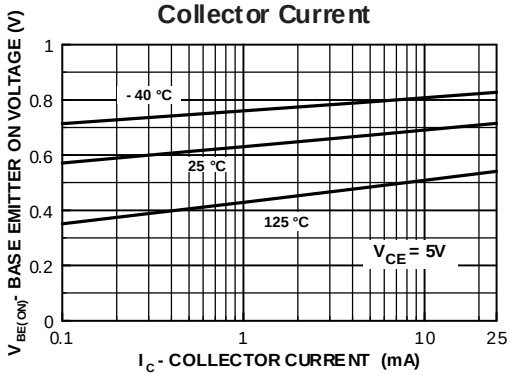
Collector-Emitter Saturation Voltage vs Collector Current



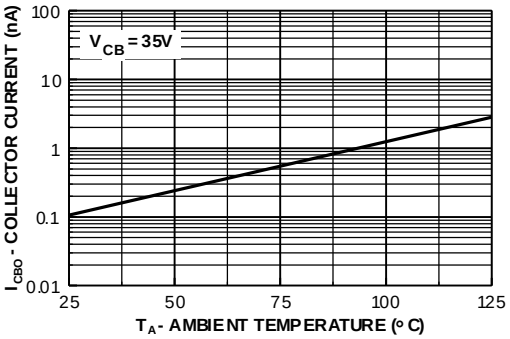
Base-Emitter Saturation Voltage vs Collector Current



Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Input and Output Capacitance vs Reverse Bias Voltage